



# S8 8 800B26PT

## '8 j cXY!8 j cXY' Modules

Symbol	Test Conditions	Characteristic Values	Unit
$I_R$	$T_{VJ}=T_{VJM}; V_R=V_{RRM}$	50	mA
$V_F$	$I_F=2400A; T_{VJ}=25^{\circ}C$	1.28	V
$V_{FO}$	For power-loss calculations only	0.8	V
$r_F$	$T_{VJ}=T_{VJM}$	0.2	m $\Omega$
$Q_S$	$T_{VJ}=125^{\circ}C; I_F=300A; -di/dt=50A/us$	1850	$\mu C$
$I_{RM}$		165	A
$R_{thJC}$	per diode; DC current per module	0.0405 0.02025	K/W
$R_{thJK}$	per diode; DC current per module	0.010 0.005	K/W
$d_s$	Creepage distance on surface	12.7	mm
$d_A$	Strike distance through air	9.6	mm
$a$	Maximum allowable acceleration	50	m/s <sup>2</sup>

### FEATURES

- \* International standard package
- \* Copper base plate
- \* Pressure Contact Technology
- \* Isolation voltage 3600 V~
- \* UL file NO.310749
- \* RoHs compliant

### APPLICATIONS

- \* Supplies for DC power equipment
- \* DC supply for PWM inverter
- \* Field supply for DC motors
- \* Battery DC power supplies

### ADVANTAGES

- \* Space and weight savings
- \* Simple mounting
- \* Improved temperature and power cycling
- \* Reduced protection circuits



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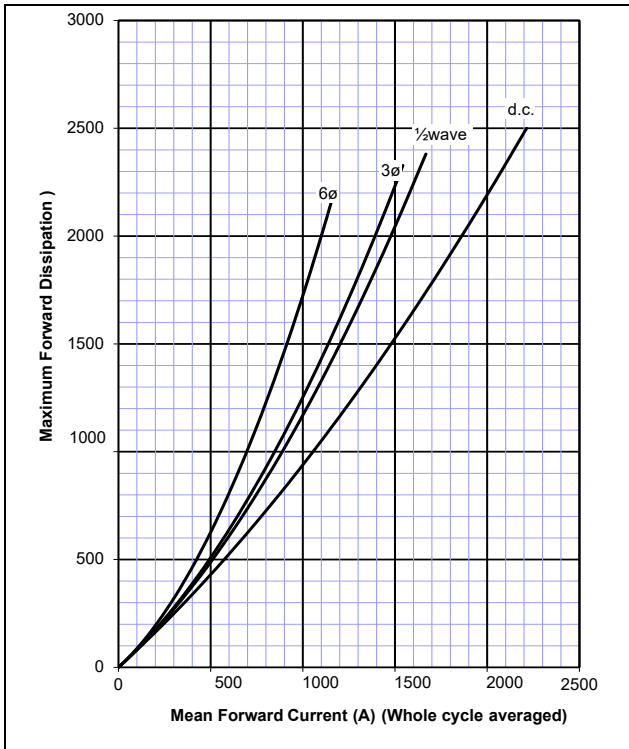


Fig.1 – On-state current vs. Power dissipation – Sine wave

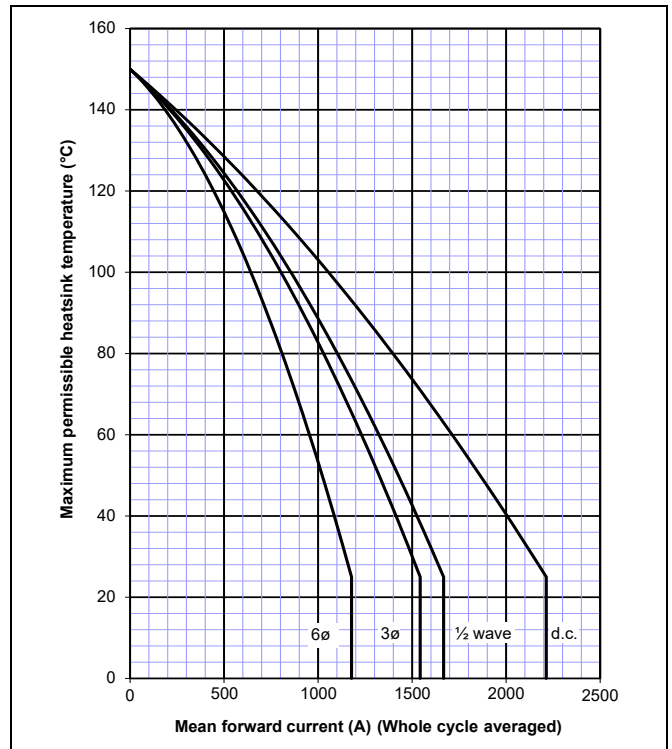


Fig.2 – On-state current vs. case temperature – Sine wave

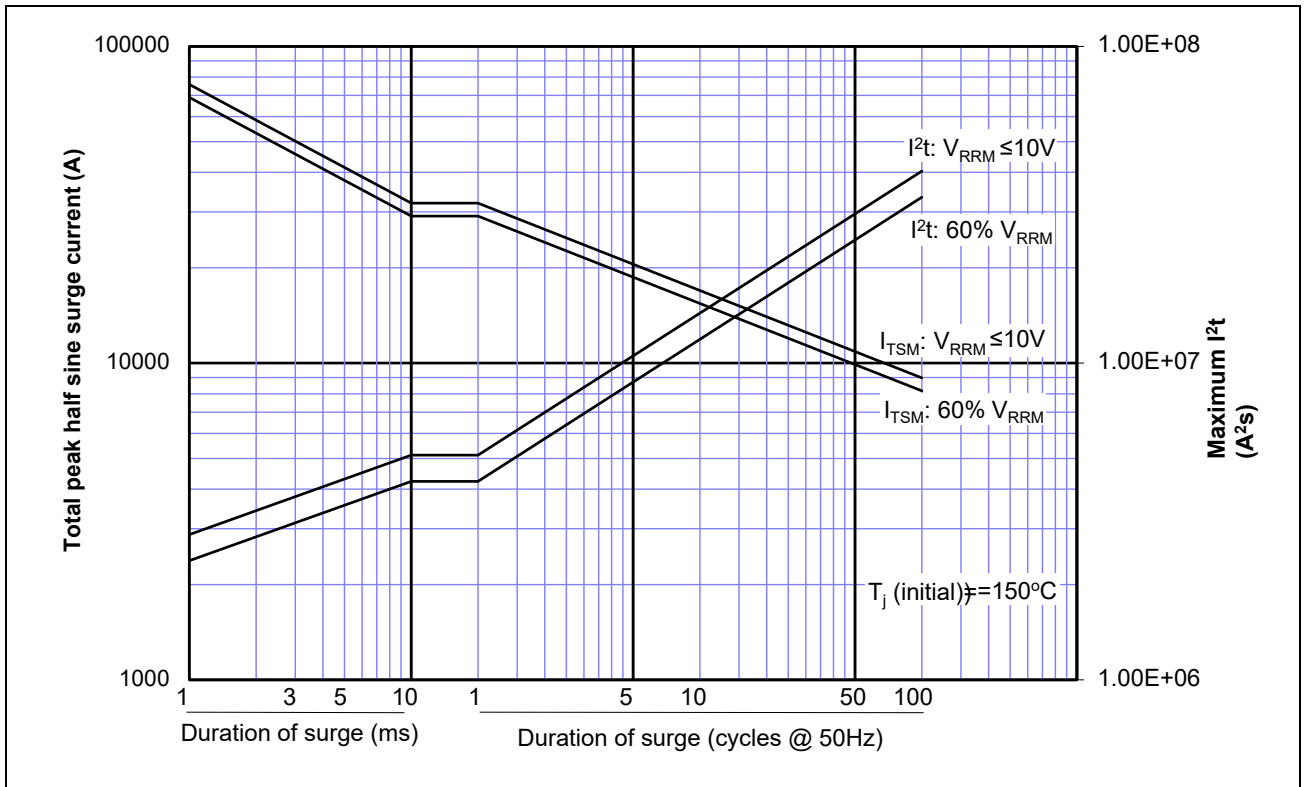


Fig.3 Maximum surge and I<sup>2</sup>t Ratings

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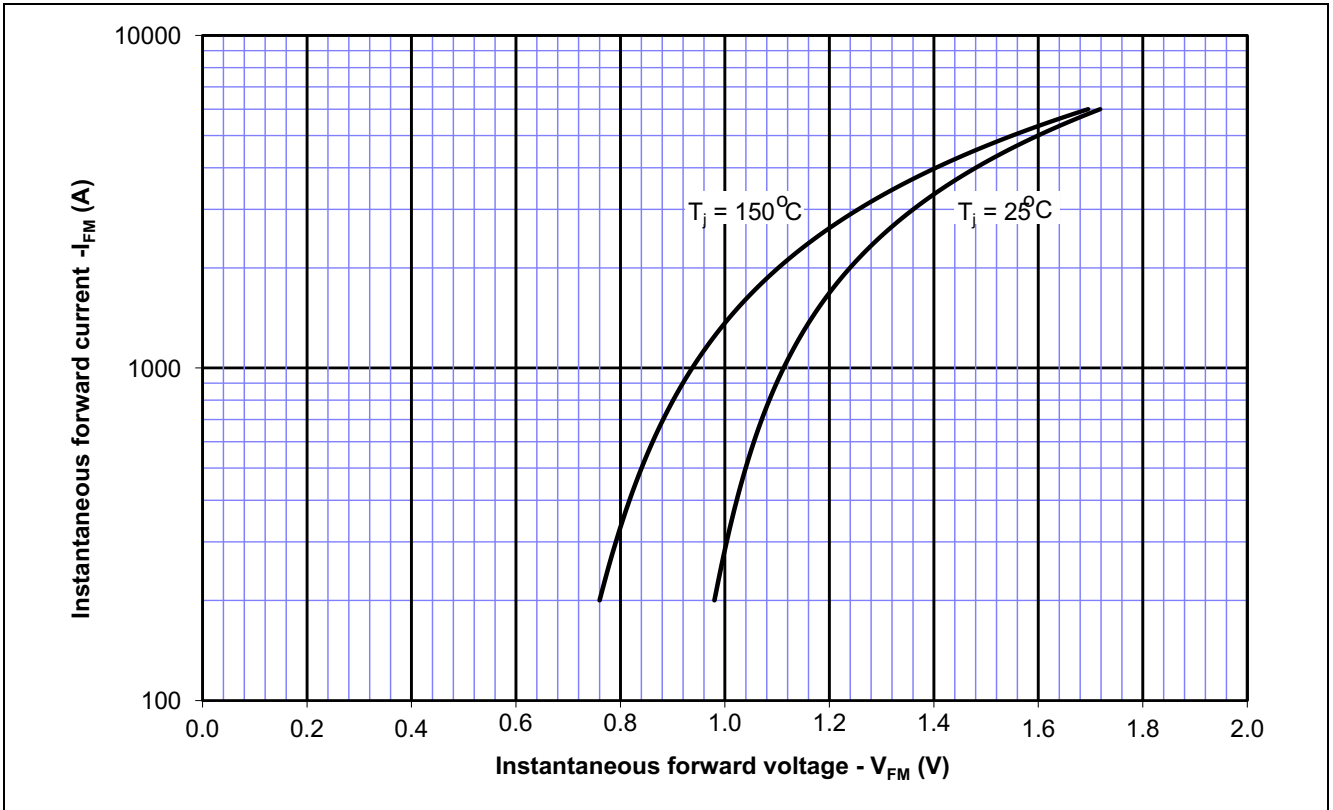


Fig.4 Forward characteristics of Limit device

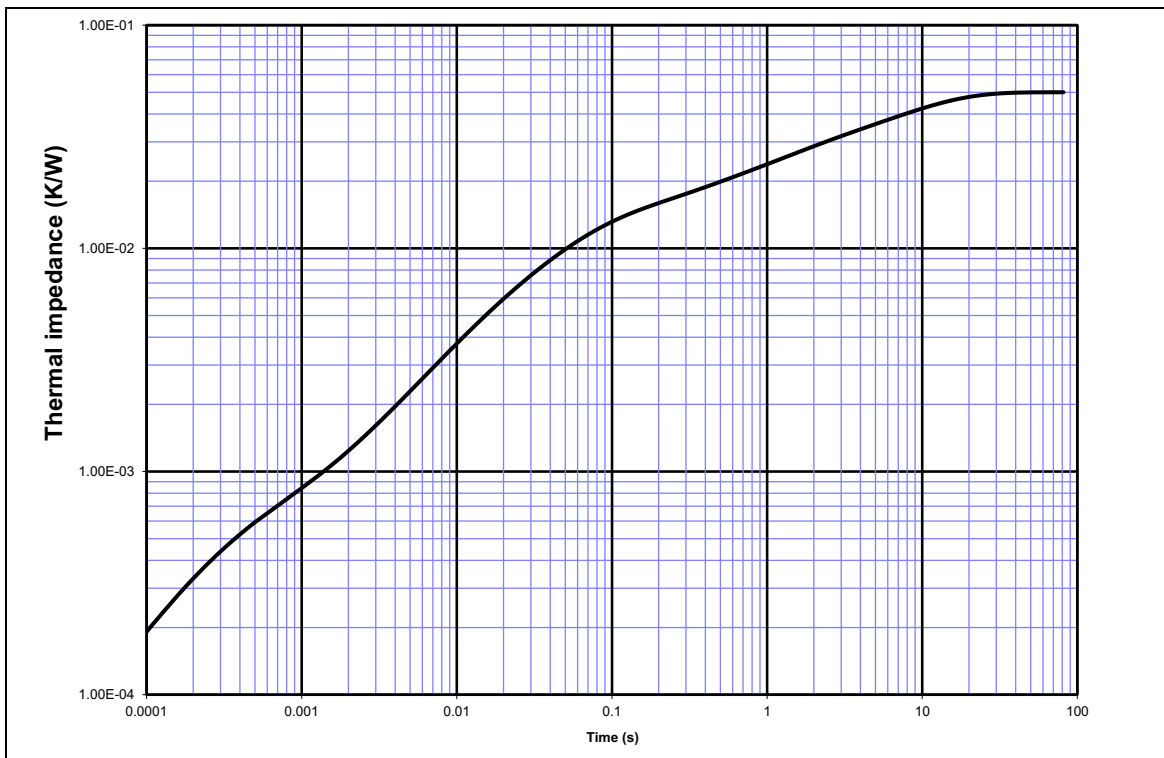


Fig.5 Transient thermal impedance